# MSKSEMI 美森科









MOV



GDT



PIFF

**B0530W-MS** 

Product specification





#### **Features**

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- High Conductance
- Also Available in Lead Free Version

### **Reference News**

PACKAGE OUTLINE	PIN Configuration	MARKING
	<b>○</b> ►	SE
SOD-123		

## Maximum Ratings @Ta=25℃

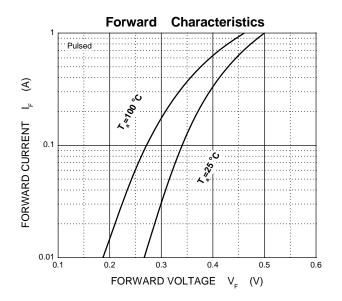
Parameter	Symbo	Value	Unit
Peak repetitive peak reverse voltage	V <sub>RRM</sub>		
Working peak reverse voltage	V <sub>RWM</sub>	30	V
DC blocking voltage	V <sub>R</sub>		
RMS reverse voltage reverse voltage (DC)	V <sub>R(RMS)</sub>	21	V
Average rectified output current	lo	0.5	Α
Non-repetitive Peak Forward Surge Current @t=8.3ms	I <sub>FSM</sub>	5.5	А
Power dissipation	P <sub>D</sub>	500	mW
Thermal resistance junction to ambient	R <sub>0JA</sub>	200	°C/W
Junction temperature	Tj	125	$^{\circ}\mathbb{C}$
Storage temperature	T <sub>STG</sub>	-55~+150	$^{\circ}$
Voltage rate of change	dv/dt	1000	V/µs

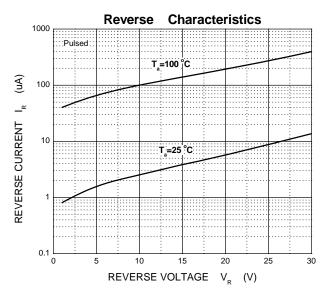
## **Electrical Characteristics @Ta=25℃**

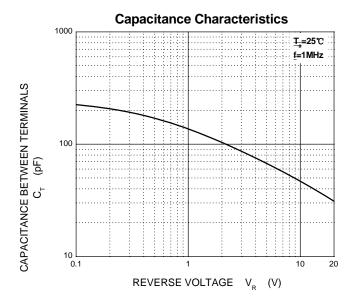
	Symbol	Test conditions	Min	Тур	Max	Unit	
Reverse breakdown voltage	V <sub>(BR)</sub>	l <sub>R</sub> =200uA	30			V	
Poverse current	l <sub>R</sub>	V <sub>R</sub> =15V			20	uA	
Reverse current		V <sub>R</sub> =30V			130	u u u	
	VF	l=0.1A			0.375	V	
Forward voltage		l⊧=0.5A			0.430		
Capacitance between terminals	Ст	V <sub>R</sub> =1,f=1MHz		170		pF	

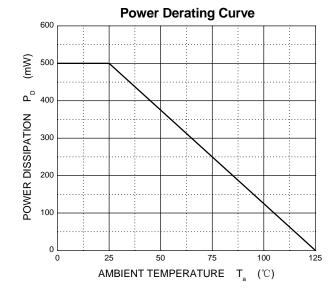


## **Typical Characteristics**



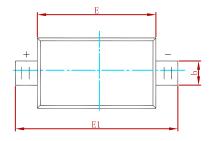


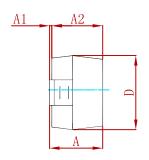


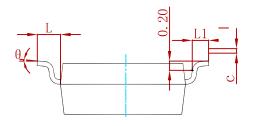




### PACKAGE MECHANICAL DATA

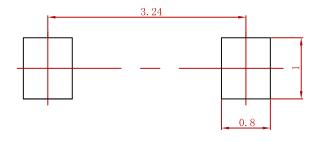






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Syllibol	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.450	0.650	0.018	0.026	
С	0.080	0.150	0.003	0.006	
D	1.500	1.700	0.059	0.067	
Е	2.600	2.800	0.102	0.110	
E1	3.550	3.850	0.140	0.152	
L	0.500 REF		0.020 REF		
L1	0.250	0.450	0.010	0.018	
θ	0°	8°	0°	8°	

## **Suggested Pad Layout**



#### Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

### **REELSPECIFICATION**

P/N	PKG	QTY
B0530W-MS	SOD-123	3000



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